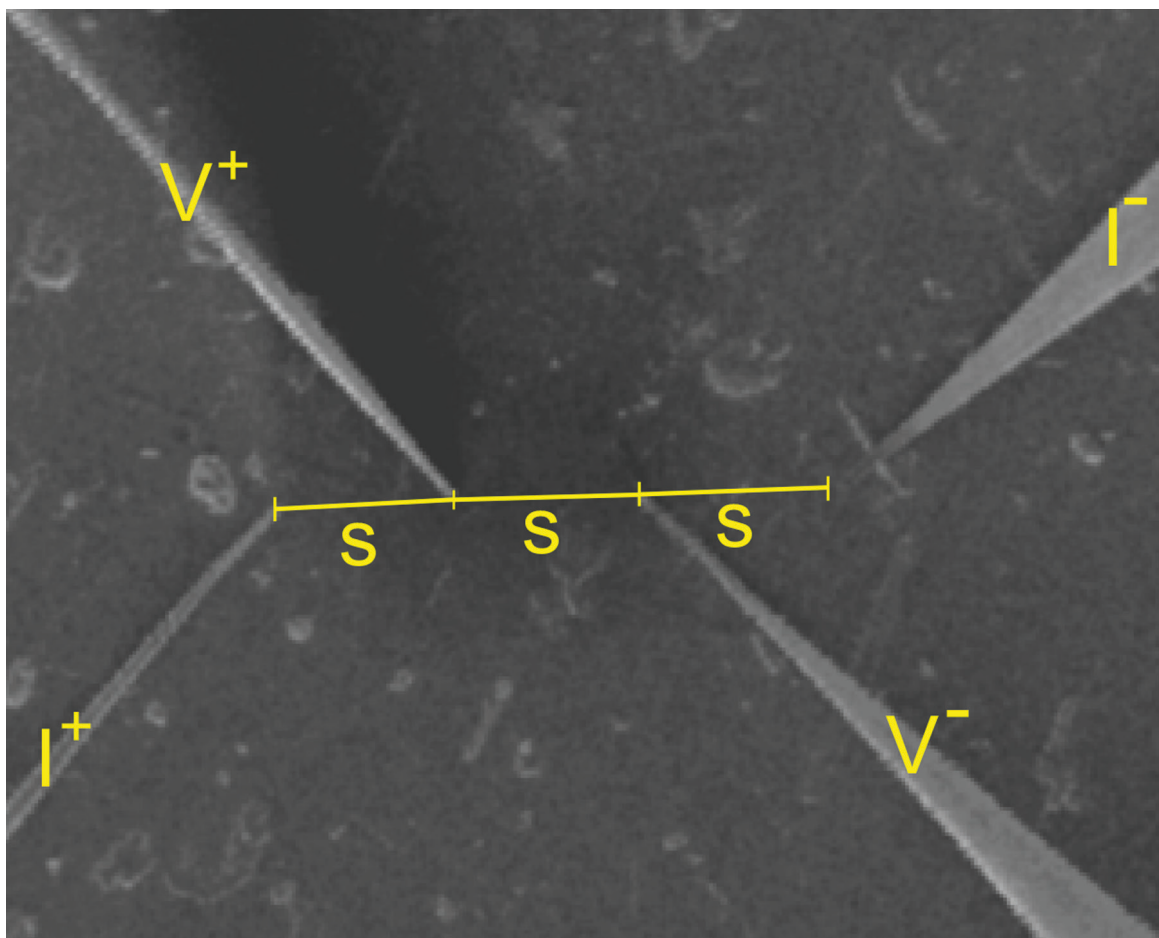




Direct measurement of anisotropic resistivity in thin films using a 4-probe STM

Tim Flatten

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